

ABSTRACT

WAFER PROCESSING METHOD

A wafer processing method for dividing a wafer along a plurality of division lines includes a step of applying a laser beam of such a wavelength as to be transmitted through the wafer to the wafer, to form division start point modified layers along the division lines; and a step of applying an external force to the wafer, to divide the wafer along the division lines, with the division start point modified layers as start points of division. At the time of forming the division start point modified layers on the back surface side of the wafer, the laser beam is applied at an output of not more than a first output, to form crack guide layers for guiding a crack extension direction as modified layers in the vicinity of the back surface, prior to the formation of the division start point modified layers, and thereafter the division start point modified layers are formed at positions equivalent to the positions of the crack guide layers.

(Figure 3B)